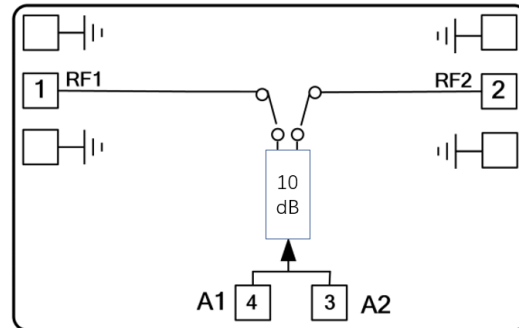


**Features**

- Frequency: DC-20GHz
- IL: 1.4dB typ.
- Att. Range: 10dB
- Control bits: 1bit
- Input /Output Return Loss: 20dB typ.
- Power Supply: -5 V
- Control Level: -5/0 V
- Die Size: 1.0 x 1.0 x 0.1 mm



**Typical Applications**

- Test Instrumentation
- Microwave Radio & VSAT
- Military & Space
- Telecom Infrastructure
- Fiber Optics

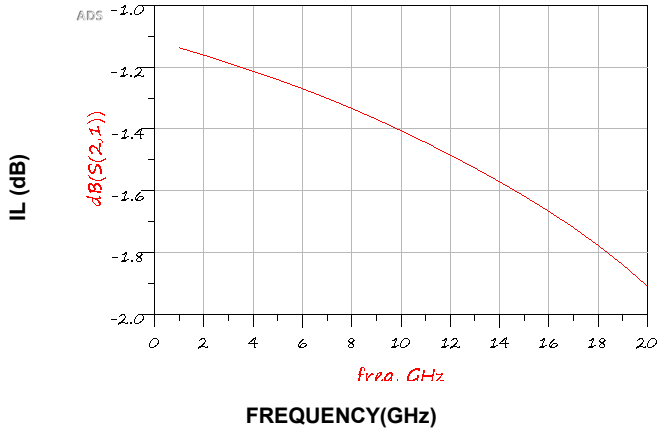
**Electrical Specifications**

TA = +25°C, VEE = -5V

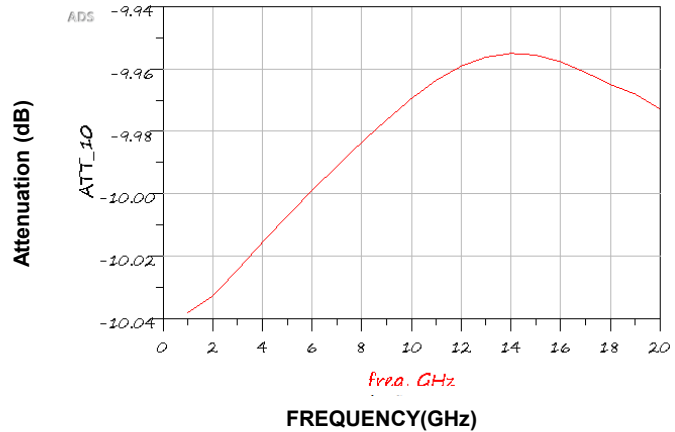
| Parameters           | Min.      | Typ. | Max. | Min. | Typ. | Max. | Min.  | Typ. | Max. | Units |
|----------------------|-----------|------|------|------|------|------|-------|------|------|-------|
| Frequency            | DC-6      |      |      | 6-18 |      |      | 18-20 |      |      | GHz   |
| IL                   |           | 1.2  |      |      | 1.4  |      |       | 1.4  |      | dB    |
| ATT Range            |           | 10.2 |      |      | 10   |      |       | 9.8  |      | dB    |
| Attenuation accuracy | ± 0.2dB   |      |      |      |      |      |       |      |      | dB    |
| Input RL             |           | 20   |      |      | 20   |      |       | 20   |      | dB    |
| Output RL            |           | 20   |      |      | 20   |      |       | 20   |      | dB    |
| Input P1dB           | 24 (typ.) |      |      |      |      |      |       |      |      | dBm   |
| Switch time          | 30 (typ.) |      |      |      |      |      |       |      |      | ns    |



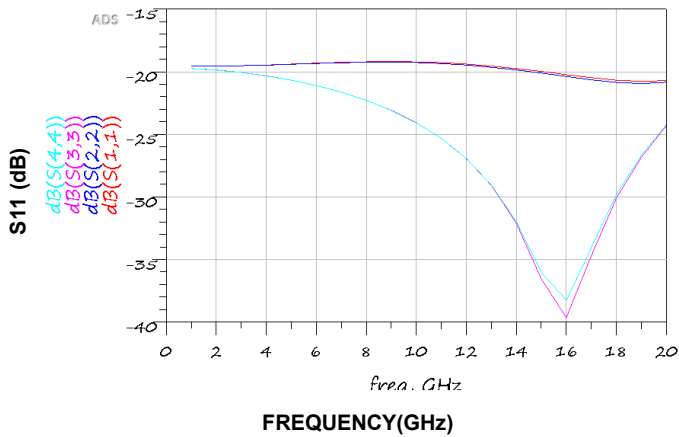
### IL vs. Frequency



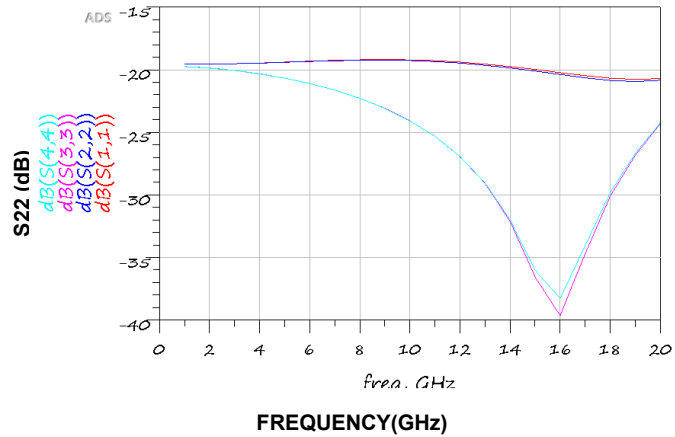
### Att. vs. Frequency



### Input RL vs. Frequency



### Output RL vs. Frequency



### Additional phase shift vs. Frequency

Additional phase shift (deg.)

FREQUENCY(GHz)

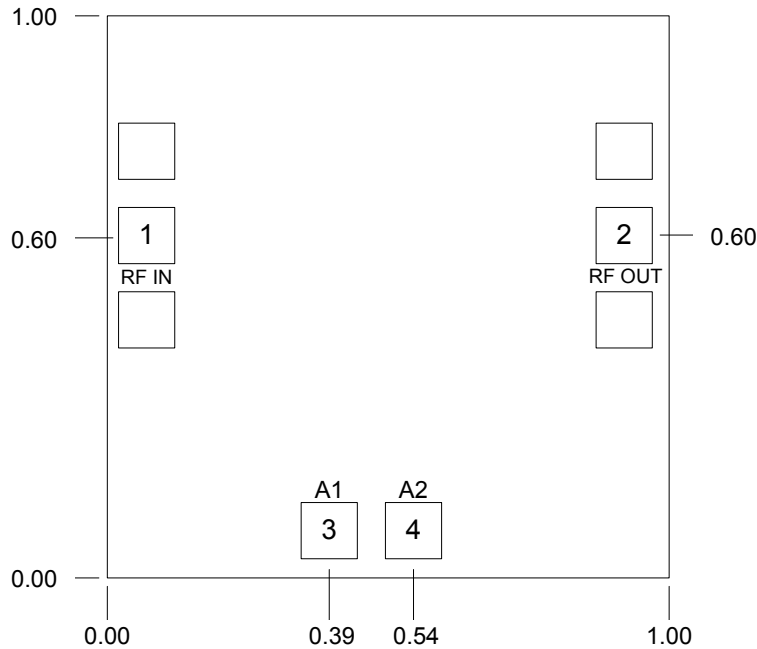
### Attenuation accuracy vs. Frequency

Attenuation accuracy (dB)

FREQUENCY(GHz)



**Outline Drawing:**  
All Dimensions in mm

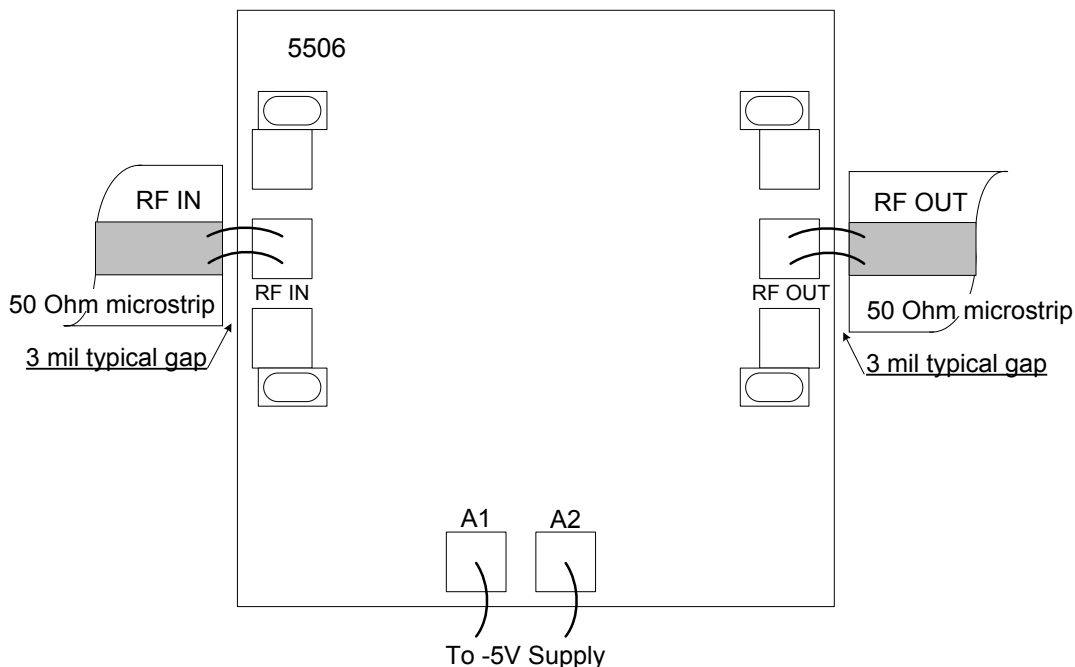


| Pad            | Function | Description   |
|----------------|----------|---|
| 1,2            | RF1, RF2 | 50 ohm circuit matched, and there is no blocking capacitor integrated inside the chip |
| 3,4            | A1, A2   | Control ports, see below the truth table  |
| Bottom of chip | GND      | The bottom of the chip should be in good contact with the RF and DC ground            |

| Status    | A1  | A2  |
|-----------|-----|-----|
| Reference | 0V  | -5V |
| 10dB      | -5V | 0V  |



## Assembly Drawing



### Notes:

1. Die thickness: 100um
2. Typical bond pad is 100\*100  $\mu\text{m}^2$
3. Bond pad metalization: Gold
4. Backside metalization: Gold
5. Backside of the die (GND)
6. No connection required for unlabeled bond pads
7. Internal DC Block at both input and output.
8. Input/Output use two 25um gold wire, length less than 250um is recommended.

### Maximum Ratings:

1. Input power: +24dBm
2. Operating temperature: -55°C to +85°C
3. Storage temperature: -65°C to +150°C